



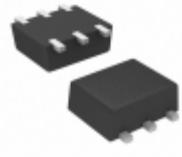




	<h2>SI1065X-T1-E3</h2>
	<p>Hersteller-Teilenummer: SI1065X-T1-E3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 12V 1.18A SOT563F</p> <p>Datenblätter:  SI1065X-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 46439 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1065X-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 12V 1.18A SOT563F
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	46439 pcs Stock
detaillierte Beschreibung	P-Channel 12V 236mW (Ta) Surface Mount SC-89-6
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-563, SOT-666
Supplier Device-Gehäuse	SC-89-6
Verlustleistung (max)	236mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	-
Rds On (Max) @ Id, Vgs	156 mOhm @ 1.18A, 4.5V
VGS (th) (Max) @ Id	950mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	10.8nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	480pF @ 6V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI1065X-T1-E3TR

SI1065X-T1-E3 ist neu im Original, Suche SI1065X-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1065X-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI1065X-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI1064-A-GM Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 36-WFQFN</p>	 <p>SI1065X-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 1.18A SC89-6</p>	 <p>SI1065-A-GM Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 36-WFQFN</p>	 <p>SI1067X-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 1.06A SC89-6</p>
 <p>SI1067X-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 1.06A SOT563F</p>	 <p>SI1065-A-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 36-WFQFN</p>	 <p>SI1065X-T1-GE3 Vishay / Siliconix MOSFET P-CH 12V 1.18A SC89-6</p>	 <p>SI1064-A-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 36-WFQFN</p>

heiße Teile

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SI1039X-T1-E3	SI1040X-T1-E3	SI1040X-T1-E3	SI1040X-T1-GE3	SI1040X-T1-GE3
SI1041ADY	SI1041DY-T1	SI1041DY-T1-E3	SI1045AB	SI1045ADY-T1
SI1046X-T1-E3	SI1046X-T1-GE3	SI1046X-T1-GE3	SI1050X-T1-E3	SI1050X-T1-E3
SI1050X-T1-GE3	SI1050X-T1-GE3	SI1051X-T1-GE3	SI1051X-T1-GE3	SI1056X-T1-E3
SI1056X-T1-E3	SI1056X-T1-GE3	SI1056X-T1-GE3	SI1058X-T1-GE3	SI1058X-T1-GE3
SI1065X-T1-E3	SI1065X-T1-GE3	SI1065X-T1-GE3	SI1067X-T1-E3	SI1067X-T1-E3
SI1067X-T1-GE3	SI1067X-T1-GE3	SI1069X-T1-E3	SI1069X-T1-E3	SI1069X-T1-GE3
SI1069X-T1-GE3	SI1070X-T1-E3	SI1070X-T1-E3	SI1070X-T1-GE3	SI1070X-T1-GE3
SI1071X-T1-GE3	SI1071X-T1-GE3	SI1072X-T1-E3	SI1072X-T1-E3	SI1072X-T1-GE3
SI1072X-T1-GE3	SI1073X-T1-GE3	SI1073X-T1-GE3	SI1120-A-GMR	SI1132-A10-GMR

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